AMENDMENT

Claim Amendments

1.   (canceled)

2.   (canceled)

3.   (canceled)

4.   (canceled)

5.   (canceled)

6.   (canceled)

7.   (canceled)

8.   (canceled)

9.   (canceled)

10.   (currently amended) A method of forming a continuous isolation region of controlled doping level in a substrate below an active region of a snapback device, comprising

using forming a perforated mask with multiple perforations over a silicon substrate,

implanting dopant through the mask to define multiple spotted implants in the substrate, and

annealing the device to cause the multiple spotted implants to form the continuous isolation region, wherein the relative size and separation of the perforations in the mask is controlled to control the dopant density of the isolation region during doping of the isolation region.

11.   (canceled)

12.   (original) A method of claim 10, further comprising exposing the device to one or more predefined elevated temperatures for predefined times.

3.

....Page 3

13.   (currently amended) A method of controlling ~~increasing~~ the breakdown voltage of a

    snapback device comprising

        forming an isolation layer in a substrate of said snapback device, and

        thereafter forming an active region above the isolation layer, wherein forming the

isolation layer includes forming spotted implants in the substrate and annealing the device

to cause ~~causing~~ the spotted implants substantially to combine to form said isolation

region, the size and separation of the spotted implants is chosen to provide an isolation

region of desired doping density.

14.   (original) A method of claim 13, wherein the spotted implants are formed by making

    use of a mask with intermittent openings.

15.   (original) A method of claim 13, wherein the spotted implants are provided before one

    or both of an epitaxial layer being grown and high diffusion drive taking place.

16.   (original) A method of claim 13, wherein the snapback device is an ESD protection

    device.

17.   (canceled)

18.   (original) A method of claim 13, further comprising exposing the device to one or

    more predefined elevated temperatures for predefined times.